Maurice S Skolnick

List of Publications by Year
in descending order

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672	24,053	7551 77	13727 129
papers	citations	h-index	g-index

676	676	676	9677
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Engineering Chiral Lightâ€“Matter Interactions in a Waveguide-Coupled Nanocavity. ACS Photonics, 2022, 9, 706-713.	3.2	8
2	Condensation of 2D exciton-polaritons in an open-access microcavity. Journal of Applied Physics, 2022, 131, 093101.	1.1	3
3	Few-photon all-optical phase rotation in a quantum-well micropillar cavity. Nature Photonics, 2022, 16, 566-569.	15.6	13
4	Optical analogue of Dresselhaus spinâ€“orbit interaction in photonic graphene. Nature Photonics, 2021, 15, 193-196.	15.6	35
5	Ultrafast-nonlinear ultraviolet pulse modulation in an AlInGaN polariton waveguide operating up to room temperature. Nature Communications, 2021, 12, 3504.	5.8	15
6	Experimental observation of topological Z2 exciton-polaritons in transition metal dichalcogenide monolayers. Nature Communications, 2021, 12, 4425.	5.8	42
7	Excitonâ€“polaritons in GaAs-based slab waveguide photonic crystals. Applied Physics Letters, 2021, 119, 181101.	1.5	3
8	Optical and magnetic control of orbital flat bands in a polariton Lieb lattice. Physical Review A, 2021, 104, .	1.0	1
9	Highly nonlinear trion-polaritons in a monolayer semiconductor. Nature Communications, 2020, 11, 3589.	5.8	83
10	Photon Statistics of Filtered Resonance Fluorescence. Physical Review Letters, 2020, 125, 043603.	2.9	28
11	Strong coupling of excitons in 2D MoSe2/hBN heterostructure with optical bound states in the continuum. Journal of Physics: Conference Series, 2020, 1461, 012012.	0.3	1
12	A semiconductor topological photonic ring resonator. Applied Physics Letters, 2020, 116, .	1.5	34
13	Nonlinear polaritons in a monolayer semiconductor coupled to optical bound states in the continuum. Light: Science and Applications, 2020, 9, 56.	7.7	124
14	Chiral topological photonics with an embedded quantum emitter. Optica, 2020, 7, 1690.	4.8	86
15	Electrically tunable trion-polaritons in MoSe2/hBN heterostructure integrated with a photonic crystal slab. AIP Conference Proceedings, 2020, , .	0.3	0
16	Pulse control protocols for preserving coherence in dipolar-coupled nuclear spin baths. Nature Communications, 2019, 10, 3157.	5.8	15
17	Light Scattering from Solid-State Quantum Emitters: Beyond the Atomic Picture. Physical Review Letters, 2019, 123, 167403.	2.9	26
18	Measurement of local optomechanical properties of a direct bandgap 2D semiconductor. APL Materials, 2019, 7, .	2.2	18

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19	Tunable Photon Statistics Exploiting the Fano Effect in a Waveguide. Physical Review Letters, 2019, 122, 173603.	2.9	30
20	Complete characterization of GaAs gradient-elastic tensors and reconstruction of internal strain in GaAs/AlGaAs quantum dots using nuclear magnetic resonance. Physical Review B, 2019, 99, .	1.1	5
21	Direct Measurement of Hyperfine Shifts and Radio Frequency Manipulation of Nuclear Spins in Individual CdTe/ZnTe Quantum Dots. Physical Review Letters, 2019, 122, 096801.	2.9	6
22	Effect of photonic spin-orbit coupling on the topological edge modes of a Su-Schrieffer-Heeger chain. Physical Review B, 2019, 99, .	1.1	34
23	Spatiotemporal continuum generation in polariton waveguides. Light: Science and Applications, 2019, 8, 6.	7.7	16
24	Amplification of nonlinear polariton pulses in waveguides. Optics Express, 2019, 27, 10692.	1.7	2
25	Exciton Polaritons in a Two-Dimensional Lieb Lattice with Spin-Orbit Coupling. Physical Review Letters, 2018, 120, 097401.	2.9	120
26	Transition from Propagating Polariton Solitons to a Standing Wave Condensate Induced by Interactions. Physical Review Letters, 2018, 120, 167402.	2.9	12
27	Quantum fluids of light in acoustic lattices. Journal Physics D: Applied Physics, 2018, 51, 033001.	1.3	4
28	Valley coherent exciton-polaritons in a monolayer semiconductor. Nature Communications, 2018, 9, 4797.	5.8	66
29	Spin Domains in One-Dimensional Conservative Polariton Solitons. ACS Photonics, 2018, 5, 5095-5102.	3.2	13
30	Polarization-resolved strong lightâ€“matter coupling in planar GaAs/AlGaAs waveguides. Optics Letters, 2018, 43, 4526.	1.7	10
31	Electrical control of nonlinear quantum optics in a nano-photonic waveguide. Optica, 2018, 5, 644.	4.8	20
32	Electro-mechanical control of an on-chip optical beam splitter containing an embedded quantum emitter. Optics Letters, 2018, 43, 2142.	1.7	13
33	High Purcell factor generation of indistinguishable on-chip single photons. Nature Nanotechnology, 2018, 13, 835-840.	15.6	178
34	Formation of a macroscopically occupied polariton state in a tunable open-access microcavity under resonant excitation. Journal of Applied Physics, 2018, 124, .	1.1	3
35	Nonreciprocal Transmission and Reflection of a Chirally Coupled Quantum Dot. Nano Letters, 2018, 18, 5475-5481.	4.5	19
36	Cross calibration of deformation potentials and gradient-elastic tensors of GaAs using photoluminescence and nuclear magnetic resonance spectroscopy in GaAs/AlGaAs quantum dot structures. Physical Review B, 2018, 97, .	1.1	11

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37	On-chip electro-mechanical routing of single photons from an embedded quantum emitter. , 2018, , .		0
38	Path-dependent initialization of a single quantum dot exciton spin in a nanophotonic waveguide. Physical Review B, 2017, 95, .	1.1	20
39	Dark Solitons in High Velocity Waveguide Polariton Fluids. Physical Review Letters, 2017, 119, 097403.	2.9	61
40	Valley-addressable polaritons in atomically thin semiconductors. Nature Photonics, 2017, 11, 497-501.	15.6	169
41	Measurement of the spin temperature of optically cooled nuclei and GaAs hyperfine constants in GaAs/AlGaAs quantum dots. Nature Materials, 2017, 16, 982-986.	13.3	41
42	Backward Cherenkov radiation emitted by polariton solitons in a microcavity wire. Nature Communications, 2017, 8, 1554.	5.8	23
43	Metalorganic vapor phase epitaxy growth, transmission electron microscopy, and magneto-optical spectroscopy of individual InAsxP1â^'x/Ga0.5In0.5P quantum dots. Physical Review Materials, 2017, 1, .	0.9	1
44	Bright and Coherent On-Chip Single Photons from a Very High Purcell Factor Photonic Crystal Cavity. , 2017, , .		0
45	On-chip interference of single photons from an embedded quantum dot and an external laser. Applied Physics Letters, 2016, 108, .	1.5	19
46	Single-photon electroluminescence for on-chip quantum networks. Applied Physics Letters, 2016, 109, .	1.5	10
47	Ultra-low-power polariton solitons in semiconductor waveguides and microcavities. , 2016, , .		0
48	Dynamic vibronic coupling in InGaAs quantum dots [Invited]. Journal of the Optical Society of America B: Optical Physics, 2016, 33, C115.	0.9	9
49	Ultrafast depopulation of a quantum dot by LA-phonon-assisted stimulated emission. Physical Review B, 2016, 93, .	1.1	15
50	Vanishing electrongfactor and long-lived nuclear spin polarization in weakly strained nanohole-filled GaAs/AlGaAs quantum dots. Physical Review B, 2016, 93, .	1.1	22
51	Tuning Nonlinear Mechanical Mode Coupling in GaAs Nanowires Using Cross-Section Morphology Control. Nano Letters, 2016, 16, 7414-7420.	4.5	13
52	Chirality of nanophotonic waveguide with embedded quantum emitter for unidirectional spin transfer. Nature Communications, 2016, 7, 11183.	5.8	218
53	Full Stark control of polariton states on a spin-orbit hypersphere. Physical Review B, 2016, 94, .	1.1	7
54	Few-second-long correlation times in a quantum dot nuclear spin bath probed by frequency-comb nuclear magnetic resonance spectroscopy. Nature Physics, 2016, 12, 688-693.	6.5	16

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55	High-fidelity initialization of long-lived quantum dot hole spin qubits by reduced fine-structure splitting. Physical Review B, 2015, 92, .	1.1	19
56	Logic gates with bright dissipative polariton solitons in Bragg cavity systems. Physical Review B, 2015, 92, .	1.1	17
57	Spin Textures of Exciton-Polaritons in a Tunable Microcavity with Large TE-TM Splitting. Physical Review Letters, 2015, 115, 246401.	2.9	82
58	Tunable polaritonic molecules in an open microcavity system. Applied Physics Letters, 2015, 107, .	1.5	19
59	On-chip electrically controlled routing of photons from a single quantum dot. Applied Physics Letters, 2015, 106, .	1.5	21
60	Spatial Patterns of Dissipative Polariton Solitons in Semiconductor Microcavities. Physical Review Letters, 2015, 115, 256401.	2.9	21
61	Linearly Polarized Emission from an Embedded Quantum Dot Using Nanowire Morphology Control. Nano Letters, 2015, 15, 1559-1563.	4.5	37
62	Design and characterization of high optical quality InGaAs/GaAs/AlGaAs-based polariton microcavities. Applied Physics Letters, 2015, 106, .	1.5	8
63	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. Nature Communications, 2015, 6, 6348.	5.8	54
64	Phonon-Assisted Population Inversion of a Single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>InGaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:mrow></mml:math>Q Dot by Pulsed Laser Excitation. Physical Review Letters, 2015, 114, 137401.	2.9	124
65	Integrated photonic devices with single quantum dots. , 2015, , .		0
66	Strong exciton-photon coupling in monolayer heterostructures in tunable microcavities. , 2015, , .		0
67	Ultra-low-power hybrid lightâ€“matter solitons. Nature Communications, 2015, 6, 8317.	5.8	74
68	Excitonâ€“polaritons in van der Waals heterostructures embedded in tunable microcavities. Nature Communications, 2015, 6, 8579.	5.8	377
69	Phonon-Assisted Population Inversion of a Single Quantum Dot. , 2015, , .		0
70	Fast High-Fidelity Hole Spin Initialisation in a Single Quantum Dot at Zero Magnetic Field. , 2015, , .		0
71	Waveguide-coupled photonic crystal cavity for quantum dot spin readout. Optics Express, 2014, 22, 2376.	1.7	23
72	Strong exciton-photon coupling in open semiconductor microcavities. Applied Physics Letters, 2014, 104, .	1.5	48

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73	Monolithic integration of a quantum emitter with a compact on-chip beam-splitter. Applied Physics Letters, 2014, 104, .	1.5	47
74	Two-Dimensional Metalâ€“Chalcogenide Films in Tunable Optical Microcavities. Nano Letters, 2014, 14, 7003-7008.	4.5	129
75	Waveguide Coupled Resonance Fluorescence from On-Chip Quantum Emitter. Nano Letters, 2014, 14, 6997-7002.	4.5	75
76	GaAs integrated quantum photonic circuits. , 2014, , .		0
77	Effects of Spin-Dependent Interactions on Polarization of Bright Polariton Solitons. Physical Review Letters, 2014, 112, 046403.	2.9	47
78	Monolithic Integration of Quantum Emitter with On-chip Beam-splitter for Quantum Information Processing. , 2014, , .		0
79	Exciton-Polariton Gap Solitons in Two-Dimensional Lattices. Physical Review Letters, 2013, 111, 146401.	2.9	124
80	Element-sensitive measurement of the holeâ€“nuclear spin interaction in quantum dots. Nature Physics, 2013, 9, 74-78.	6.5	70
81	Asymmetry tuning of Fano resonances in GaAs photonic crystal cavities. Applied Physics Letters, 2013, 102, .	1.5	11
82	Spontaneous vortices in optically shaped potential profiles in semiconductor microcavities. Physical Review B, 2013, 87, .	1.1	10
83	Exciton polaritons in semiconductor waveguides. Applied Physics Letters, 2013, 102, .	1.5	54
84	Homogeneous Array of Nanowire-Embedded Quantum Light Emitters. Nano Letters, 2013, 13, 861-865.	4.5	40
85	Enhanced photocurrent readout for a quantum dot qubit by bias modulation. Applied Physics Letters, 2013, 102, 181108.	1.5	4
86	IIIâ€“V quantum light source and cavity-QED on Silicon. Scientific Reports, 2013, 3, 1239.	1.6	33
87	Dynamic nuclear polarization in InGaAs/GaAs and GaAs/AlGaAs quantum dots under nonresonant ultralow-power optical excitation. Physical Review B, 2013, 88, .	1.1	16
88	Optical control of the emission direction of a quantum dot. Applied Physics Letters, 2013, 103, .	1.5	28
89	An on-chip cross-waveguide QD spin-photon interface and its applications. , 2013, , .		0
90	Effect of polariton-polariton interactions on the excitation spectrum of a nonequilibrium condensate in a periodic potential. Physical Review B, 2013, 87, .	1.1	29

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91	Interfacing Spins in an InGaAs Quantum Dot to a Semiconductor Waveguide Circuit Using Emitted Photons. Physical Review Letters, 2013, 110, 037402.	2.9	119
92	Bright Polariton Solitons and Soliton Trains. , 2013, , .		0
93	Wavefunction of polariton condensates in a tunable acoustic lattice. New Journal of Physics, 2012, 14, 075011.	1.2	11
94	Restoring mode degeneracy in H1 photonic crystal cavities by uniaxial strain tuning. Applied Physics Letters, 2012, 100, .	1.5	42
95	Disorder-limited photon propagation and Anderson-localization in photonic crystal waveguides. Applied Physics Letters, 2012, 101, 051116.	1.5	14
96	Fast preparation of a single-hole spin in an InAs/GaAs quantum dot in a Voigt-geometry magnetic field. Physical Review B, 2012, 85, .	1.1	34
97	Polarization-resolved resonant fluorescence of a single semiconductor quantum dot. Applied Physics Letters, 2012, 101, 251118.	1.5	0
98	Solitons in semiconductor microcavities. Nature Photonics, 2012, 6, 204-204.	15.6	3
99	Coherent optical control a single hole spin in a quantum dot. , 2012, , .		0
100	Planar Waveguide Architecture for the Implementation of a Network of Optically Controlled Quantum Dot Spin Qubits. , 2012, , .		0
101	Observation of bright polariton solitons in a semiconductor microcavity. Nature Photonics, 2012, 6, 50-55.	15.6	237
102	Coherent Optical Control of the Spin of a Single Hole in an<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:math>Quantum Dot. Physical Review Letters, 2012, 108, 017402.	2.9	96
103	Structural analysis of strained quantum dots using nuclear magnetic resonance. Nature Nanotechnology, 2012, 7, 646-650.	15.6	65
104	Effect of a GaAsP Shell on the Optical Properties of Self-Catalyzed GaAs Nanowires Grown on Silicon. Nano Letters, 2012, 12, 5269-5274.	4.5	31
105	Coexisting Polariton Condensates and Their Temporal Coherence in Semiconductor Microcavities. Springer Series in Solid-state Sciences, 2012, , 147-171.	0.3	0
106	Dynamic exciton-polariton macroscopic coherent phases in a tunable dot lattice. Physical Review B, 2012, 86, .	1.1	18
107	Excitonâ€“Polariton Coupling with Acoustic Phonons. Springer Series in Solid-state Sciences, 2012, , 289-306.	0.3	0
108	Direct Measurement of the Hole-Nuclear Spin Interaction in Single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InP</mml:mi><mml:mo>/</mml:mo><mml:mi>GaInP</mml:mi></mml:math>Quantum Dots Using Photoluminescence Spectroscopy. Physical Review Letters, 2011, 106, 027402.	2.9	93

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109	Mode structure of coupled L3 photonic crystal cavities. Optics Express, 2011, 19, 5670.	1.7	50
110	Charge control in InP/(Ga,In)P single quantum dots embedded in Schottky diodes. Physical Review B, 2011, 84, .	1.1	13
111	Splitting and lasing of whispering gallery modes in quantum dot micropillars. , 2011, , .		0
112	Purcell-enhanced single-photon emission from an InP quantum dot coupled to GaInP photonic crystal nanocavity. Proceedings of SPIE, 2011, , .	0.8	0
113	Polariton Condensation In One- And Two- Dimensional Acoustic Lattices. AIP Conference Proceedings, 2011, , .	0.3	0
114	Fano Resonance in GaAs 2D Photonic Crystal Nanocavities. AIP Conference Proceedings, 2011, , .	0.3	1
115	Fast control of nuclear spin polarization in an optically pumped single quantum dot. Nature Materials, 2011, 10, 844-848.	13.3	31
116	Effects of the piezoelectric field on the modulation of excitonâ€“polaritons by surface acoustic waves. Superlattices and Microstructures, 2011, 49, 233-240.	1.4	14
117	Light-polarization-independent nuclear spin alignment in a quantum dot. Physical Review B, 2011, 83, .	1.1	11
118	Suppression of Zeeman Splitting of the Energy Levels of Exciton-Polariton Condensates in Semiconductor Microcavities in an External Magnetic Field. Physical Review Letters, 2011, 106, 257401.	2.9	57
119	Unpolarized H1 photonic crystal nanocavities fabricated by stretched lattice design. Applied Physics Letters, 2011, 98, .	1.5	17
120	Stark spectroscopy and radiative lifetimes in single self-assembled CdTe quantum dots. Physical Review B, 2011, 83, .	1.1	17
121	Effect of detuning on the phonon induced dephasing of optically driven InGaAs/GaAs quantum dots. Journal of Applied Physics, 2011, 109, 102415.	1.1	20
122	Time resolved spectroscopy on quantum dots and graphene at the FELBE free-electron laser. Proceedings of SPIE, 2011, , .	0.8	0
123	Intensity damping of Rabi-oscillations and renormalization of the Rabi frequency in InGaAs/GaAs quantum dots. , 2011, , .		1
124	Superfluidity in polariton condensates. Journal of Physics: Conference Series, 2010, 210, 012060.	0.3	2
125	Inversion recovery measurements of exciton fine-structure beats in a single quantum dot. Journal of Physics: Conference Series, 2010, 245, 012010.	0.3	2
126	Growth of low density InP/GaInP quantum dots. Journal of Physics: Conference Series, 2010, 245, 012061.	0.3	3

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127	Optimization of low density InP/GaInP quantum dots for single-dot studies. Journal of Physics: Conference Series, 2010, 245, 012093.	0.3	2
128	Quantum key distribution system in standard telecommunications fiber using a short wavelength single photon source. Journal of Applied Physics, 2010, 107, .	1.1	25
129	Two-color two-photon Rabi oscillation of biexciton in single InAs/GaAs quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2485-2488.	1.3	12
130	One dimensional confinement of microcavity polaritons using non-piezoelectric surface acoustic waves. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2548-2551.	1.3	5
131	Persistent currents and quantized vortices in a polariton superfluid. Nature Physics, 2010, 6, 527-533.	6.5	282
132	Quantum Confined Stark Effect in Single Self-Assembled CdTe Quantum Dots. , 2010, , .		0
133	Observation of Quantum Hydrodynamic Effects in Microcavity Polaritons. , 2010, , .		0
134	CdTe Quantum Dots in a Field Effect Structure: Photoluminescence Lineshape Analysis. , 2010, , .		0
135	Polariton Condensation in Dynamic Acoustic Lattices. Physical Review Letters, 2010, 105, 116402.	2.9	173
136	Pumping of Nuclear Spins by Optical Excitation of Spin-Forbidden Transitions in a Quantum Dot. Physical Review Letters, 2010, 104, 066804.	2.9	61
137	Control of spontaneous emission from InP single quantum dots in GaInP photonic crystal nanocavities. Applied Physics Letters, 2010, 97, 181104.	1.5	13
138	Dynamics of optically induced nuclear spin polarization in individual<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>InP</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Ga</mml:mt dots. Physical Review B, 2010, 81, .	1.1	28
139	Fast high fidelity hole spin initialization in a single InGaAs quantum dot. Applied Physics Letters, 2010, 97, 061113.	1.5	30
140	Polarization Bistability and Resultant Spin Rings in Semiconductor Microcavities. Physical Review Letters, 2010, 105, 216402.	2.9	77
141	Phonon-Induced Rabi-Frequency Renormalization of Optically Driven Single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InGaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:math>Quantum Dots. Physical Review Letters, 2010, 105, 177402.	2.9	172
142	Damping of Exciton Rabi Rotations by Acoustic Phonons in Optically Excited<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InGaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:math>Quantum Dots. Physical Review Letters, 2010, 104, 017402.	2.9	258
143	Splitting and lasing of whispering gallery modes in quantum dot micropillars. Optics Express, 2010, 18, 22578.	1.7	21
144	Effect of Interactions on Vortices in a Nonequilibrium Polariton Condensate. Physical Review Letters, 2010, 104, 126402.	2.9	58

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145	Optically tunable nuclear magnetic resonance in a single quantum dot. Physical Review B, 2010, 82, .	1.1	21
146	Voltage-controlled nuclear polarization switching in a singleInxGa1âˆ'xAsquantum dot. Physical Review B, 2009, 79, .	1.1	5
147	Coexisting nonequilibrium condensates with long-range spatial coherence in semiconductor microcavities. Physical Review B, 2009, 80, .	1.1	67
148	Beating of Exciton-Dressed States in a Single Semiconductor<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>InGaAs</mml:mi><mml:mo>/</mml:mo><mml:mi>GaAs</mml:mi></mml:math>Quantum Dot. Physical Review Letters, 2009, 102, 207401.	2.9	44
149	Suppression of nuclear spin diffusion at a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>GaAs</mml:mtext><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mtext>Al</mm measured with a single quantum-dot nanoprobe. Physical Review B, 2009, 79, .	1.1	27
150	Voltage-controlled motional narrowing in a semiconductor quantum dot. New Journal of Physics, 2009, 11, 093032.	1.2	3
151	Twoâ€colour photocurrent detection technique for coherent control of a single InGaAs/GaAs quantum dot. Physica Status Solidi (B): Basic Research, 2009, 246, 824-827.	0.7	1
152	Collective fluid dynamics of a polariton condensate in a semiconductor microcavity. Nature, 2009, 457, 291-295.	13.7	494
153	Long lifetimes of quantum-dot intersublevel transitions in the terahertz range. Nature Materials, 2009, 8, 803-807.	13.3	157
154	Towards coherent optical control of a single hole spin: Rabi rotation of a trion conditional on the spin state of the hole. Solid State Communications, 2009, 149, 1458-1465.	0.9	2
155	Ultrafast all-optical switching in AlGaAs photonic crystal waveguide interferometers. Applied Physics Letters, 2009, 95, 141108.	1.5	16
156	Enhanced room-temperature quantum-dot effects in modulation-doped InAs/GaAs quantum dots. Applied Physics Letters, 2009, 95, 171902.	1.5	18
157	Picosecond Coherent Control of Dressed States in a Single Quantum Dot. , 2009, , .		0
158	Exciton warming in IIIâ€“V semiconductors and microcavities. Superlattices and Microstructures, 2008, 43, 449-453.	1.4	0
159	Ultrafast tailoring of the exciton distribution in quantum wells. Physica Status Solidi (B): Basic Research, 2008, 245, 1064-1066.	0.7	1
160	Spatial distribution of strong and weak coupled excitonâ€“polaritons in semiconductor microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2049-2052.	1.3	1
161	Electroluminescence emission from polariton states in GaAs-based semiconductor microcavities. Applied Physics Letters, 2008, 92, .	1.5	66
162	Quantum dot dipole orientation and excitation efficiency of micropillar modes. Optics Express, 2008, 16, 19201.	1.7	9

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163	Self-organization of multiple polariton-polariton scattering in semiconductor microcavities. Physical Review B, 2008, 77, .	1.1	55
164	â€‡Tuning of intraband absorption and photoresponse in self-assembled InAsâˆ•GaAs quantum dots by thermal annealing. Journal of Applied Physics, 2008, 103, 066101.	1.1	12
165	Long nuclear spin polarization decay times controlled by optical pumping in individual quantum dots. Physical Review B, 2008, 77, .	1.1	25
166	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. Physical Review B, 2008, 78, .	1.1	53
167	Intersublevel polaron dephasing in self-assembled quantum dots. Physical Review B, 2008, 77, .	1.1	22
168	Enhanced nonradiative Auger recombination in p-type modulation doped InAs/GaAs quantum dots. Applied Physics Letters, 2008, 93, .	1.5	19
169	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. Applied Physics Letters, 2008, 92, .	1.5	44
170	Nuclear spin pumping under resonant optical excitation in a quantum dot. Applied Physics Letters, 2008, 93, 073113.	1.5	13
171	Overhauser effect in individualInPâˆ•GaxIn1âˆ’xPdots. Physical Review B, 2008, 77, .	1.1	27
172	Fast Optical Preparation, Control, and Readout of a Single Quantum Dot Spin. Physical Review Letters, 2008, 100, 197401.	2.9	133
173	Intrinsic Decoherence Mechanisms in the Microcavity Polariton Condensate. Physical Review Letters, 2008, 101, 067404.	2.9	146
174	Excitonic spin lifetimes in InGaN quantum wells and epilayers. Journal of Applied Physics, 2008, 104, 053523.	1.1	2
175	Whispering gallery modes in quantum dot micropillar cavities. , 2008, , .		0
176	Investigating the Capping of InAs Quantum Dots by InGaAs. Springer Proceedings in Physics, 2008, , 259-262.	0.1	4
177	Fast Optical Preparation, Control, and Detection of a Single Hole Spin in a Quantum Dot. , 2008, , .		0
178	Controlled Rotation (C-ROT) Gate in a Single Self- Assembled Quantum Dot. , 2008, , .		0
179	Coherent control of single quantum dot exciton embedded in a photodiode. Journal of Modern Optics, 2007, 54, 1717-1722.	0.6	0
180	GROWTH AND CHARACTERIZATION OF MULTI-LAYER 1.3 Î¼m QUANTUM DOT LASERS. International Journal of Nanoscience, 2007, 06, 291-296.	0.4	1

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181	Focused ion beam etching for the fabrication of micropillar microcavities made of III-V semiconductor materials. Journal of Vacuum Science & Technology B, 2007, 25, 1197.	1.3	8
182	Singlet and triplet polaron relaxation in doubly charged self-assembled quantum dots. New Journal of Physics, 2007, 9, 259-259.	1.2	10
183	Transition from the strong- to the weak-coupling regime in semiconductor microcavities: Polarization dependence. Applied Physics Letters, 2007, 90, 201905.	1.5	20
184	Low threshold current density and negative characteristic temperature 1.3Î¼m InAs self-assembled quantum dot lasers. Applied Physics Letters, 2007, 90, 111102.	1.5	47
185	GaN hybrid microcavities in the strong coupling regime grown by metal-organic chemical vapor deposition on sapphire substrates. Journal of Applied Physics, 2007, 101, 093110.	1.1	20
186	High Q modes in elliptical microcavity pillars. Applied Physics Letters, 2007, 90, 161105.	1.5	24
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